Abstracts

High Q on-chip passive components for UTSi(R) CMOS technology

M. Megahed, R. Benton, M. Stuber, L. Lo, M. Burgener, Xiaolan Wu and J. Canyon. "High Q on-chip passive components for UTSi(R) CMOS technology." 1998 MTT-S International Microwave Symposium Digest 98.2 (1998 Vol. II [MWSYM]): 793-796.

UTSi (Ultra-Thin Silicon) on insulator technology shows the promise of full integration of digital, analog, RF, and RF matching circuitry on a single chip. It is based on standard VLSI technology. The process features excellent isolation due to the dielectric substrate, high RF performance transistors, and high quality passive elements. This paper presents the performance of the UTSi passive elements. Measurement data for resistors and capacitors are reported, as well as inductors with high Q.

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